

FIG.1A

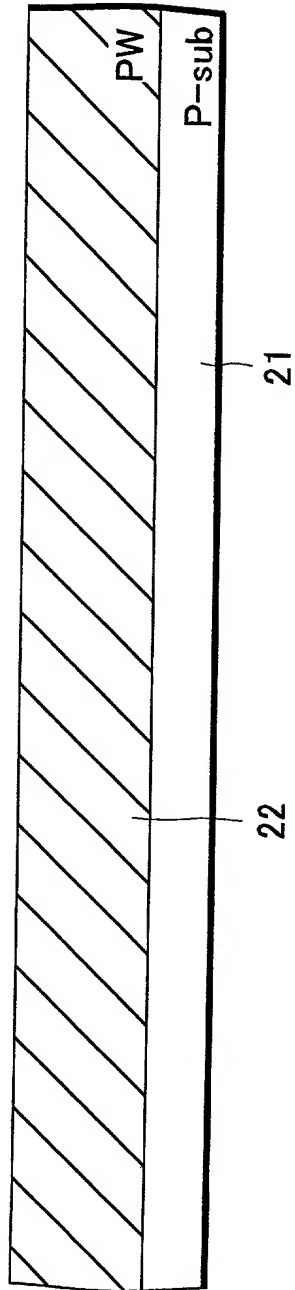


FIG.1B

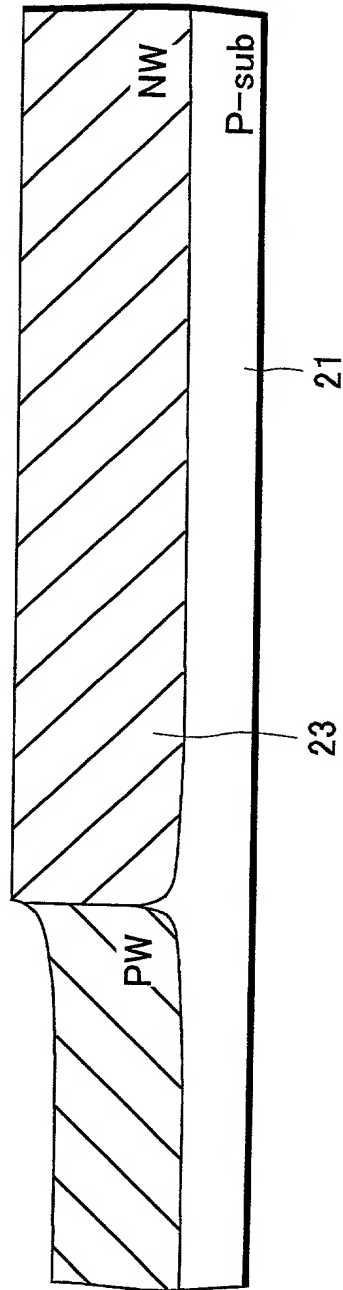


FIG.4A

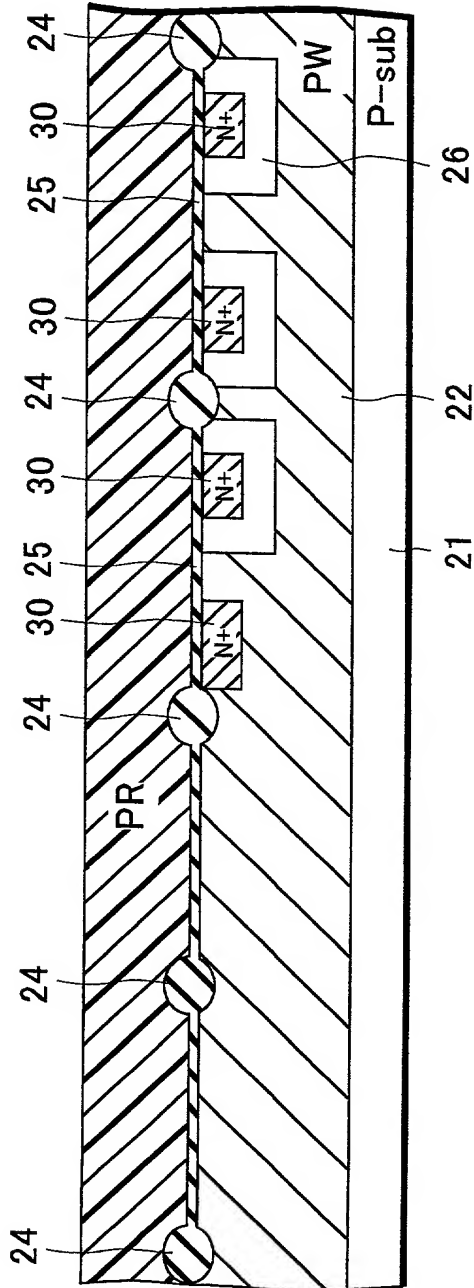


FIG.4B

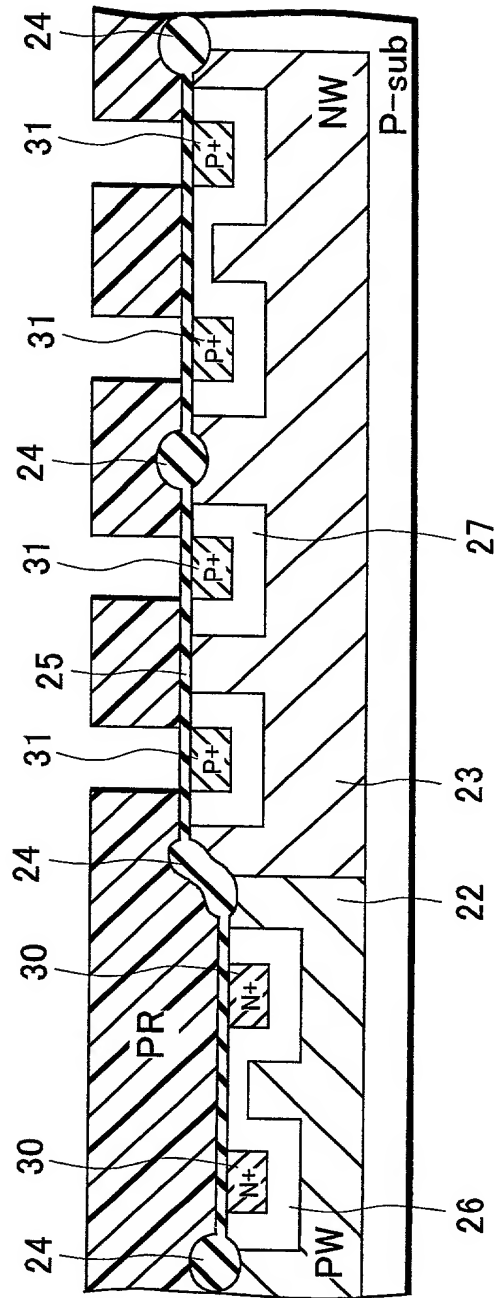


FIG.5A

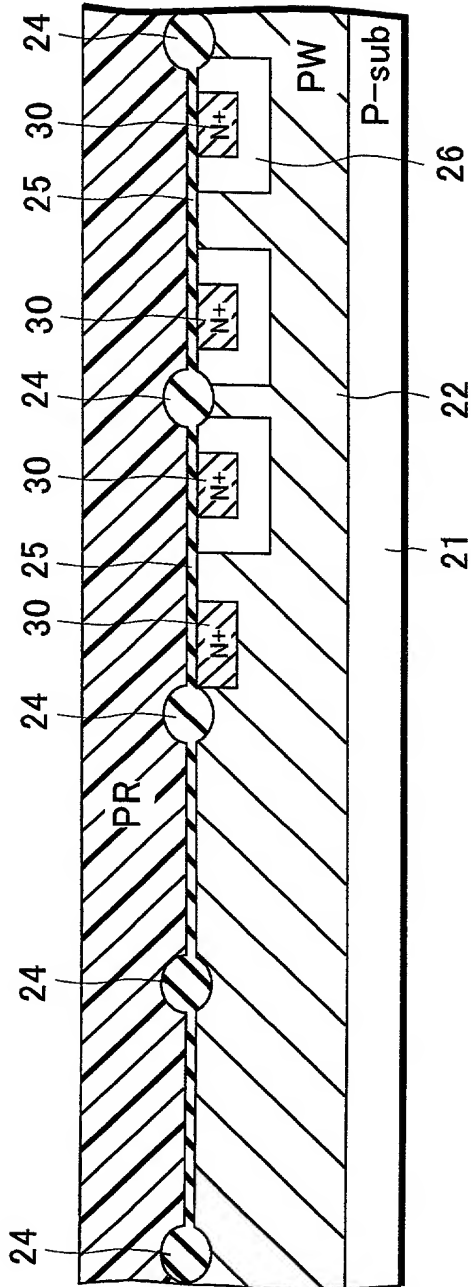


FIG.5B

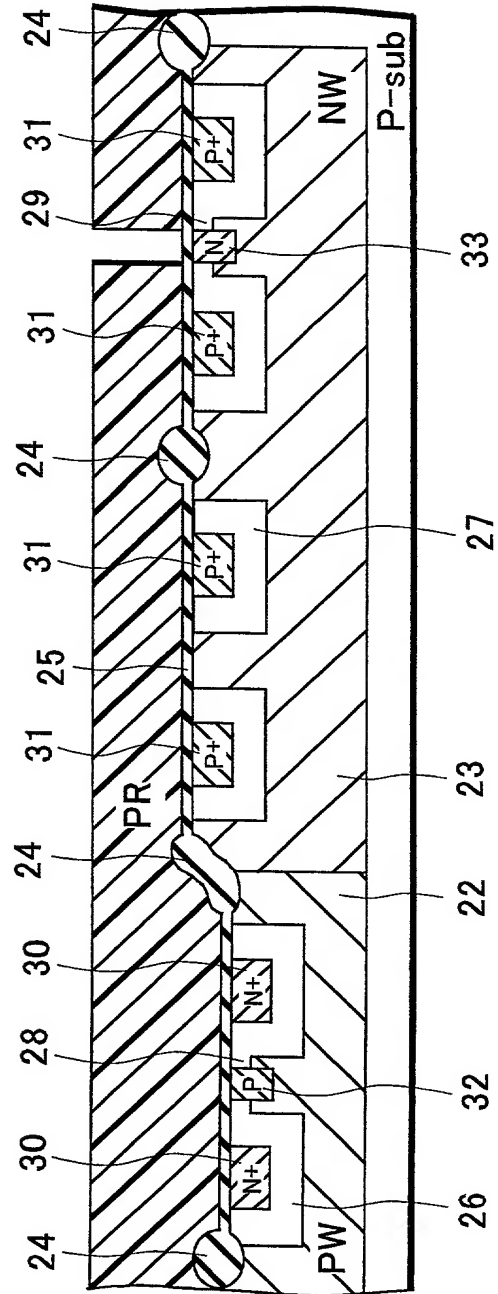


FIG.6A

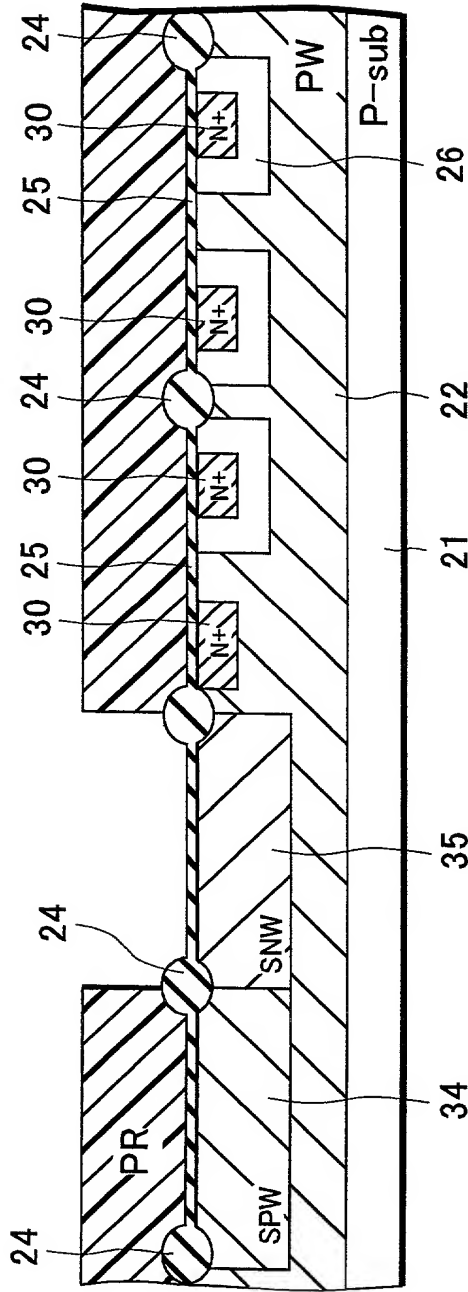


FIG.6B

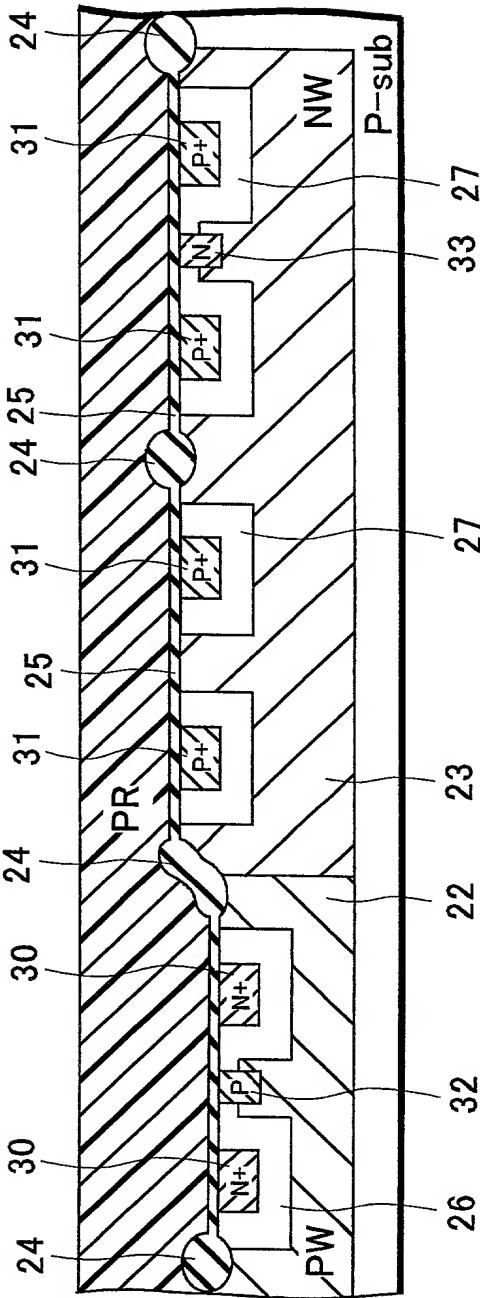


FIG. 7A

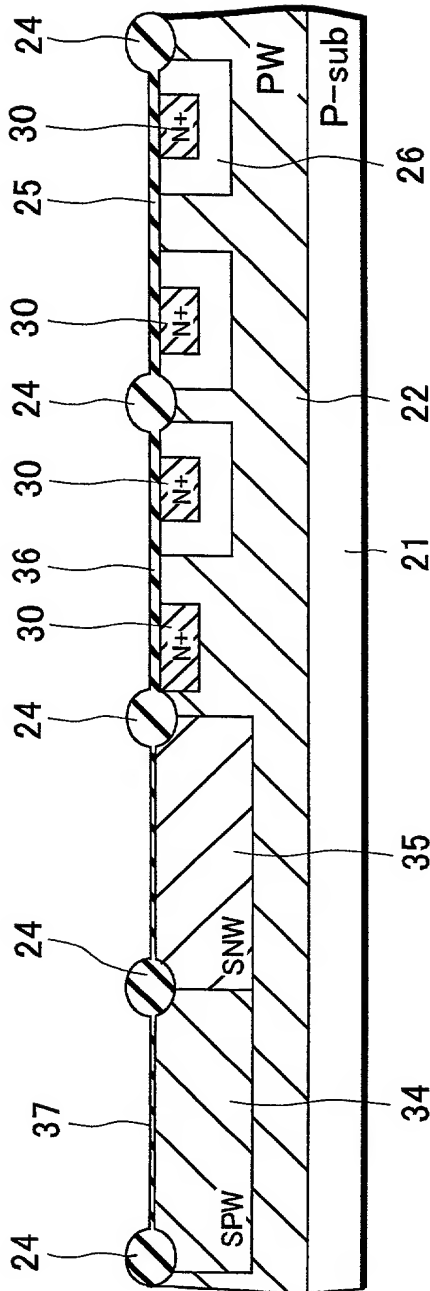


FIG. 7B

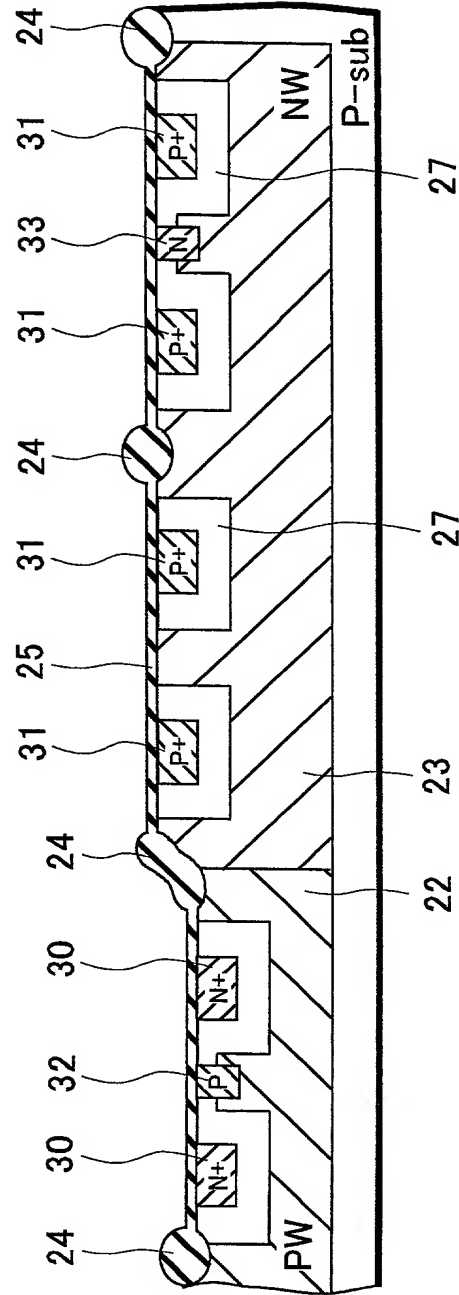


FIG.8A

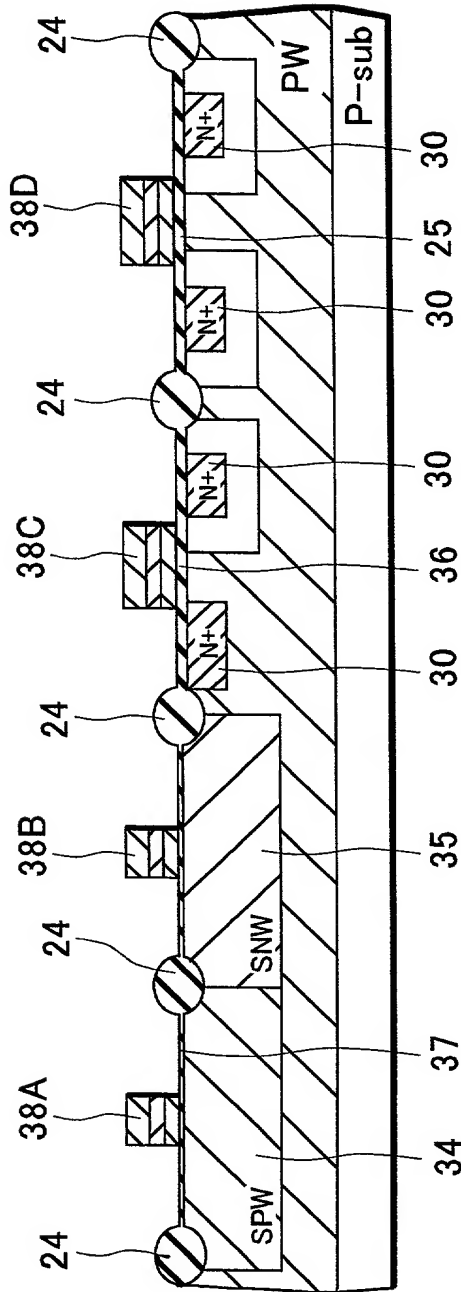


FIG.8B

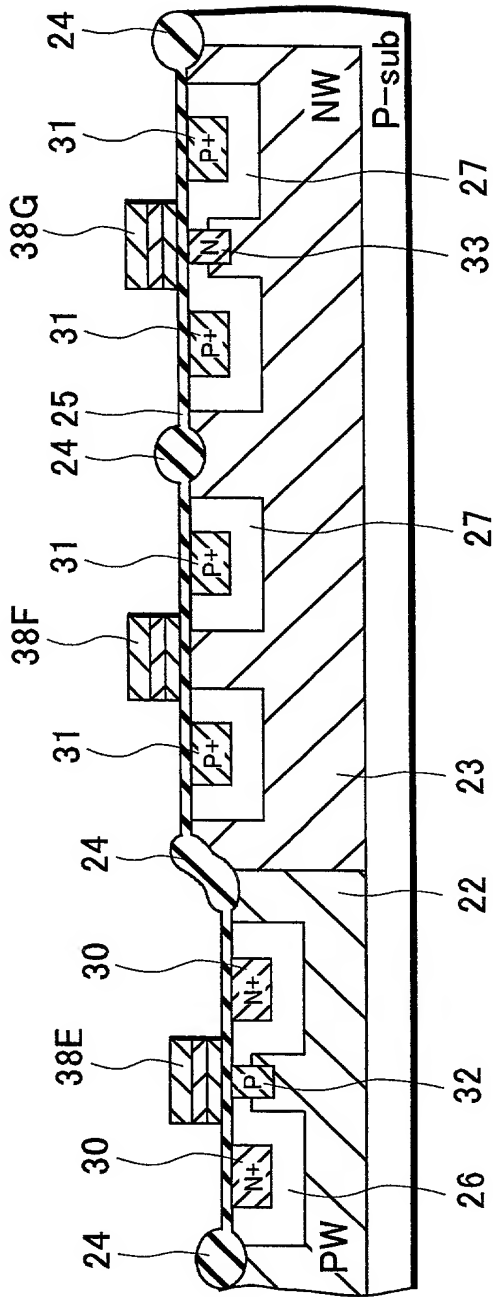


FIG.9A

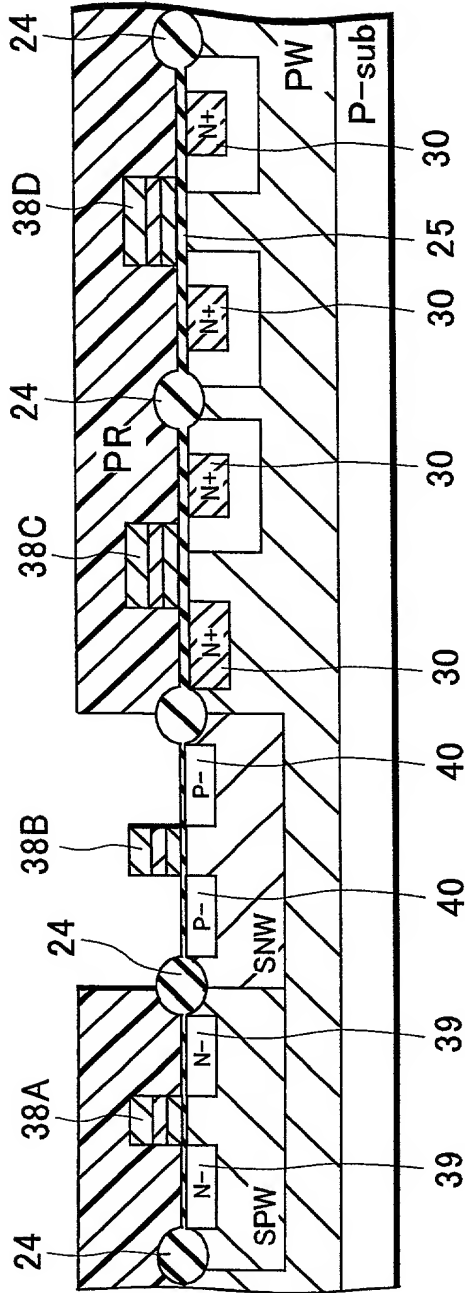
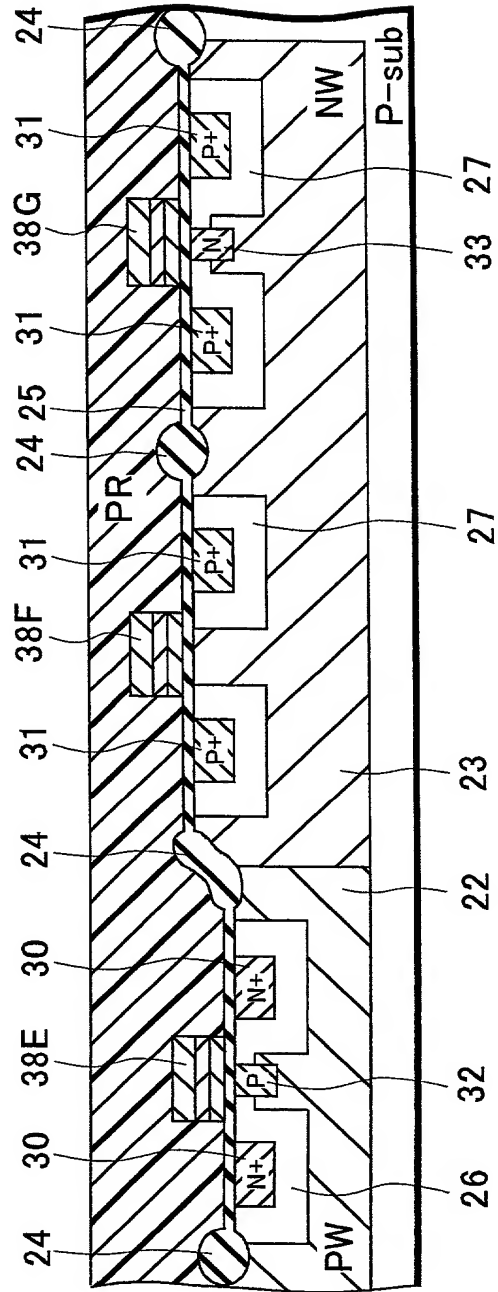


FIG.9B



This cross-sectional view illustrates a semiconductor device with a substrate 24. The device features several layers and regions: a top layer 24, a layer 38A with regions 41A and 42, a layer 38B with regions 43, 40, and 43A, a layer 38C with regions 41 and 30, a layer 38D with regions 24 and 30, and a bottom layer 24. The device includes various doped regions: N+ regions 42, 41A, 43, 40, 43A, 41, and 30; P+ regions 43, 40, 43A, 41, and 30; and P-sub regions 42, 41A, 43, 40, 43A, 41, and 30. Other labeled regions include SPW, SNW, PR, and PW. The device is shown in a cross-sectional view with a hatched pattern for the substrate 24.

[illegible]

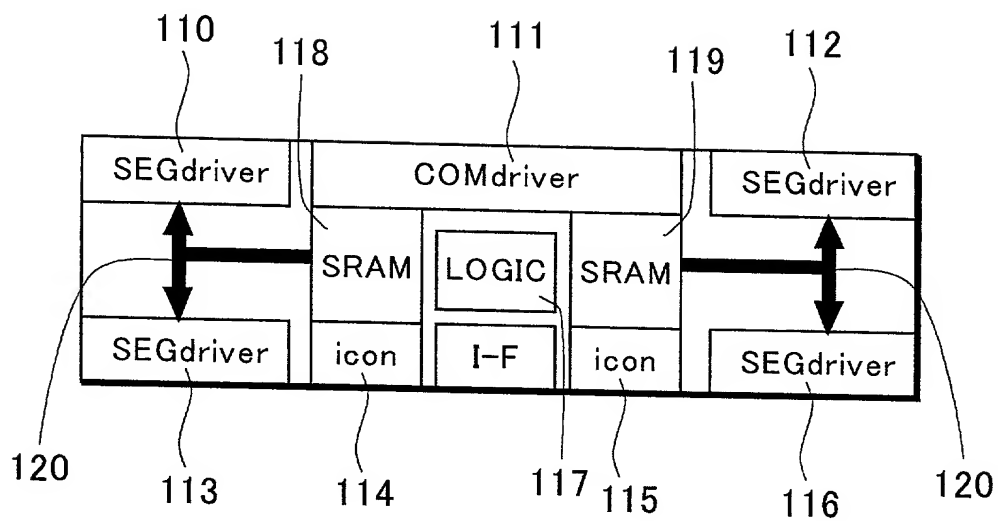
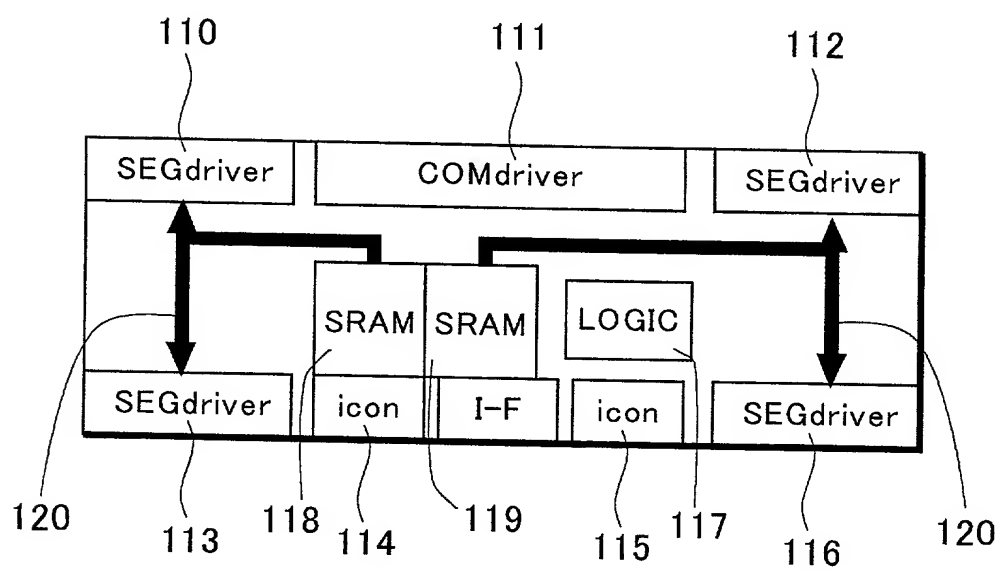
FIG. 11A**FIG. 11B**

FIG. 12

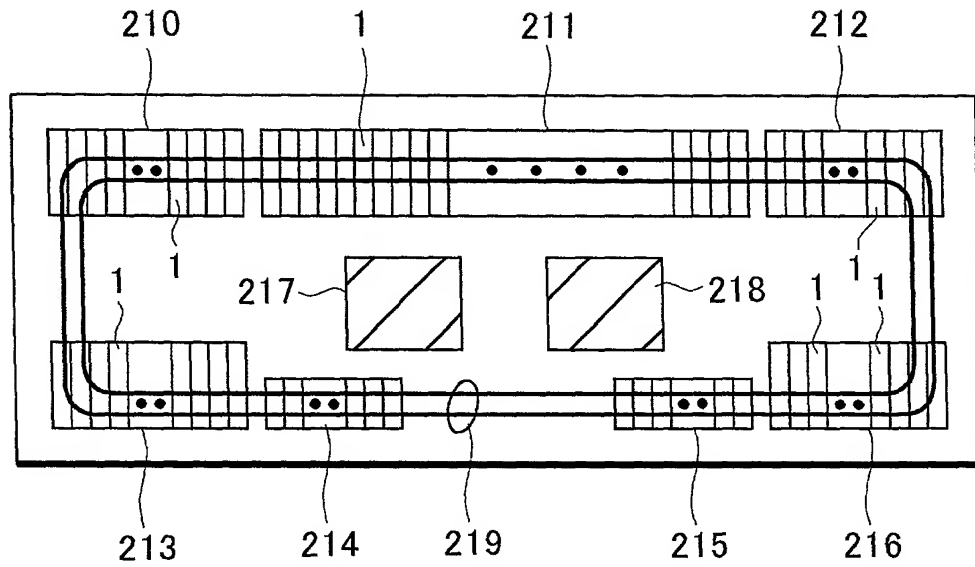


FIG. 13

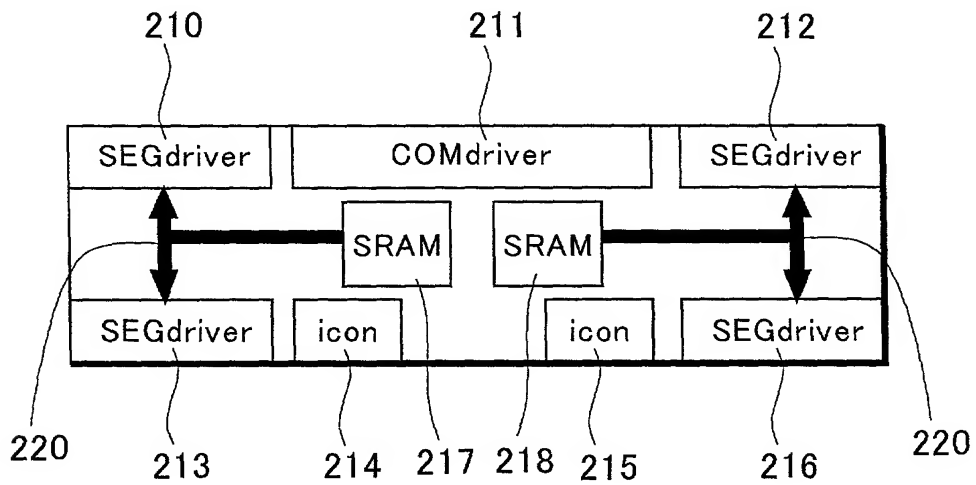


FIG. 14A

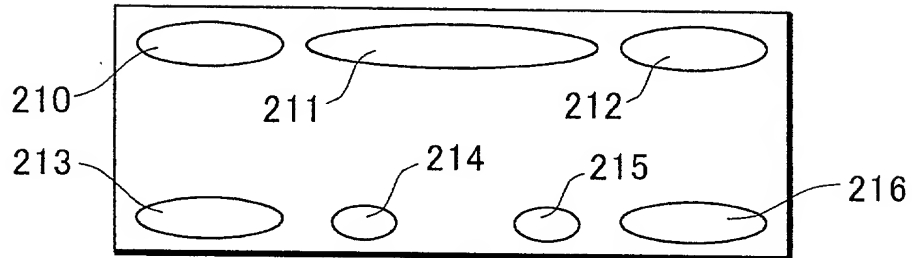


FIG. 14B

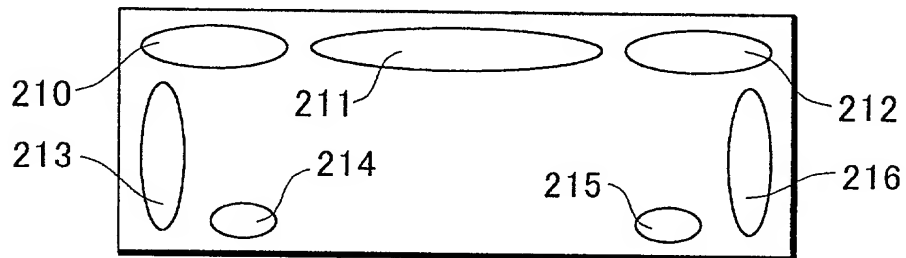


FIG. 14C

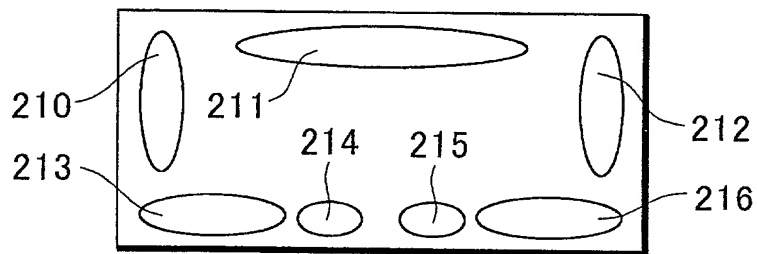


FIG. 14D

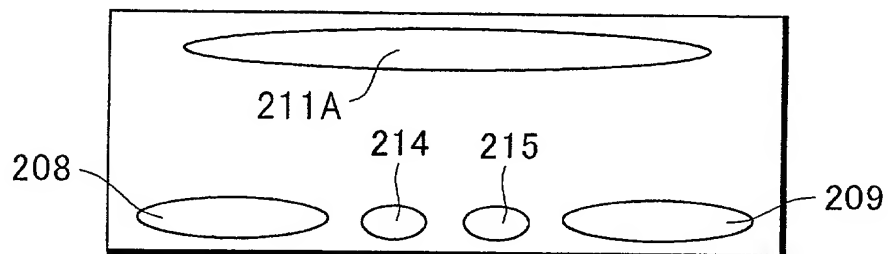


FIG. 15

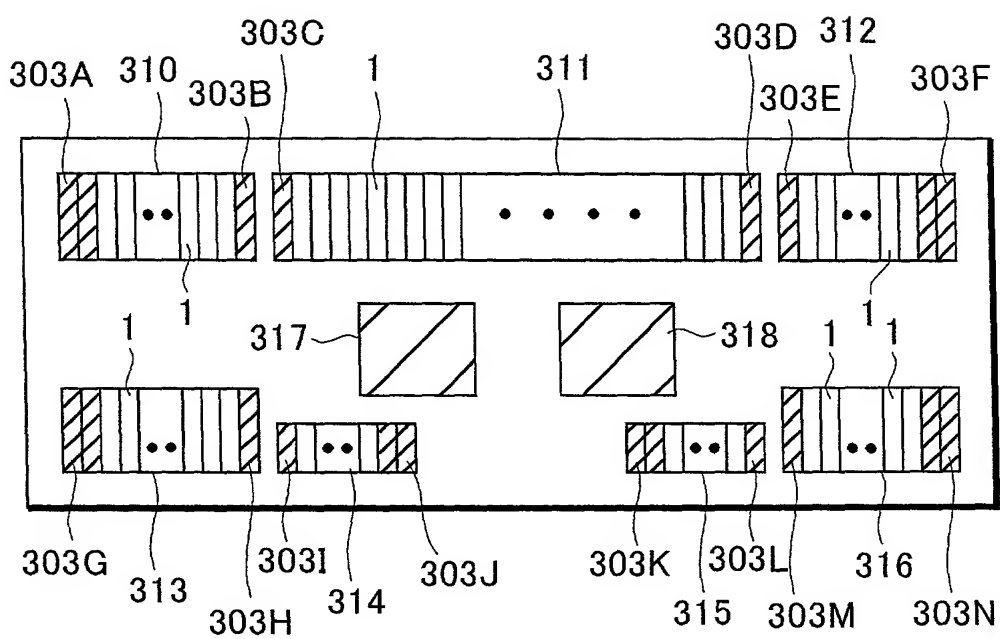


FIG. 16

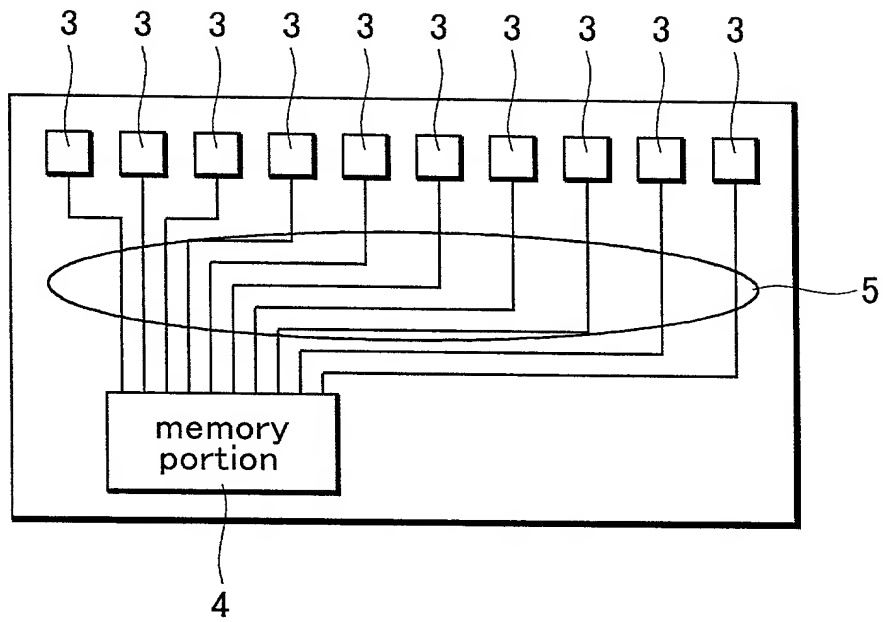


FIG.17A

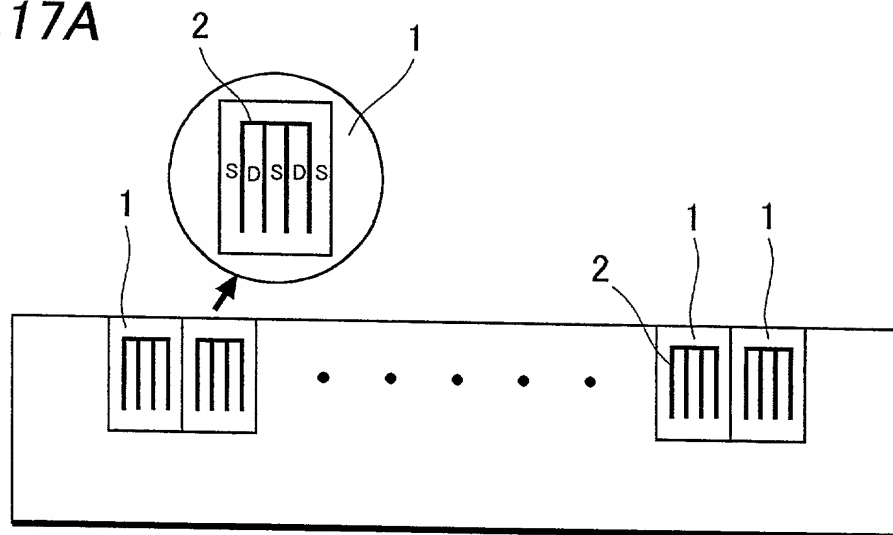


FIG.17B

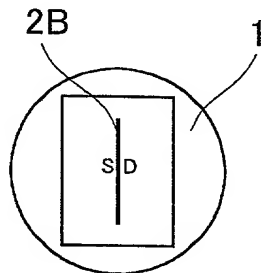


FIG.17C

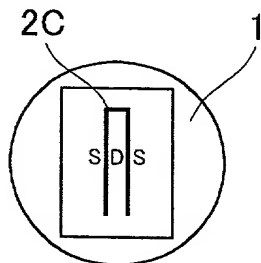


FIG.17D

